ABSTRACT

A method for forming a wiring bond pad utilized in wire bonding operations on an integrated circuit device is disclosed herein, including a wiring bond apparatus thereof. A wiring bond pad may be configured to comprise a single metal layer. At least one integrated circuit device may be positioned below the wiring bond pad to thereby conserve integrated circuit space and improve wiring bond pad efficiency as a result of configuring the wiring bond pad as a single metal layer wiring bond pad. The wiring bond pad may thus be configured as a single metal layer wiring bond pad. The single metal layer is generally located above a plurality of intermetal dielectric layers. The integrated circuit device may also be located below the plurality of intermetal dielectric layers.